Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	80	mA
				100	
I_H	I_T =500mA		MAX.	60	mA
dV/dt	V_D=400V Gate Open T_j =150		MIN.	2000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	25	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	12	μs
t_{off}				80	

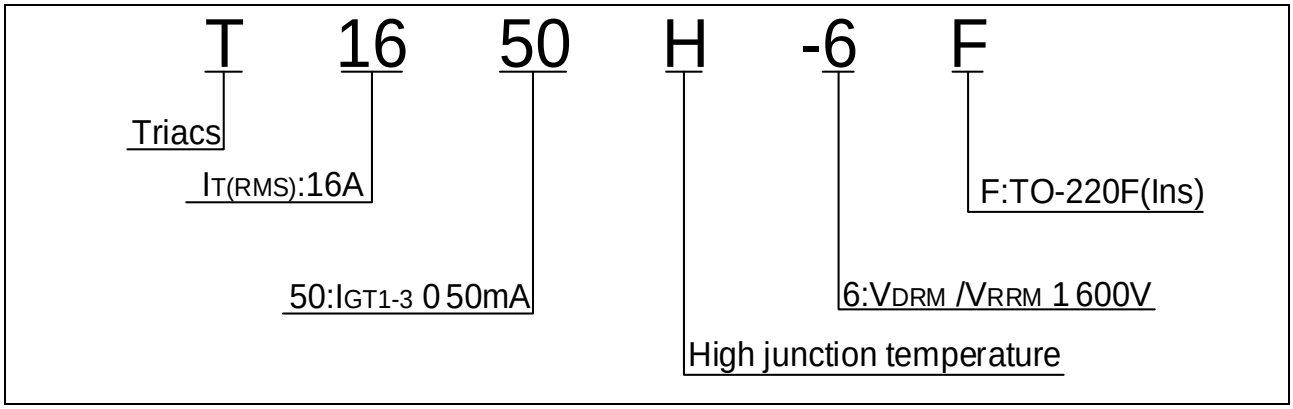
STATIC CHARACTERISTICS

V_{TM}	I_{TM} =22.5A t_p=380μs	T_j=25	1 .4	V
V_{TO}	Threshold voltage	T_j=150	0.75	V
R_D	Dynamic resistance	T_j=150	27	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=150	1 .5	mA

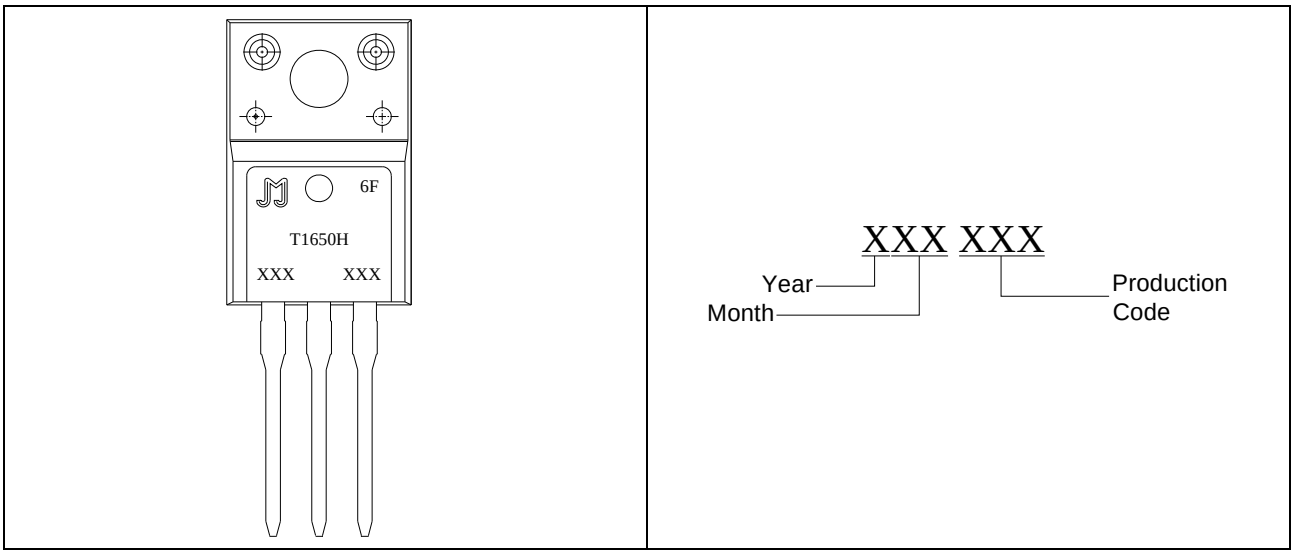
THERMAL RESISTANCES

$R_{th(j-c)}$	junction to case (AC)	2.4	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

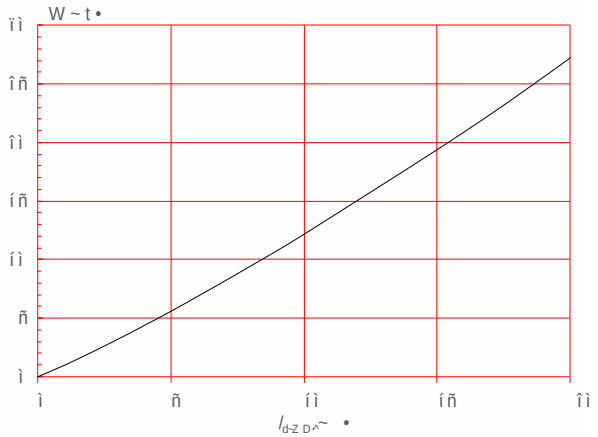
ORDERING INFORMATION



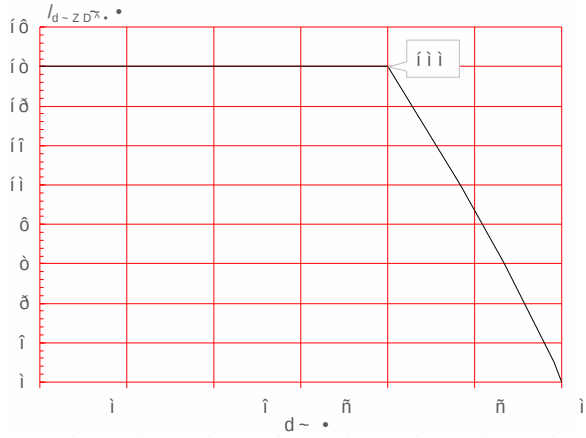
MARKING



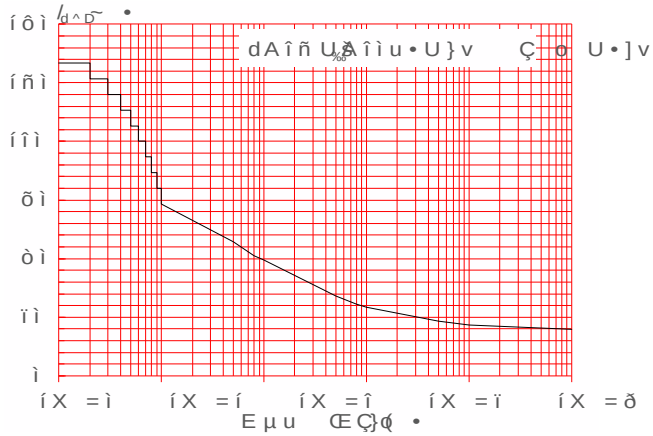
Maximum power dissipation versus RMS on-state current



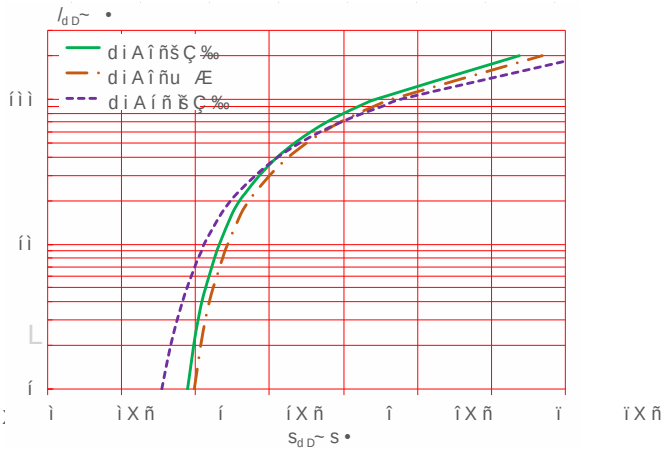
RMS on-state current versus case temperature



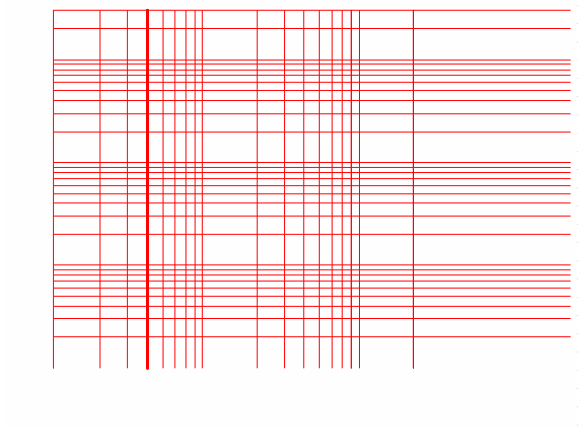
Surge peak on-state current versus number of cycles



On-state characteristics

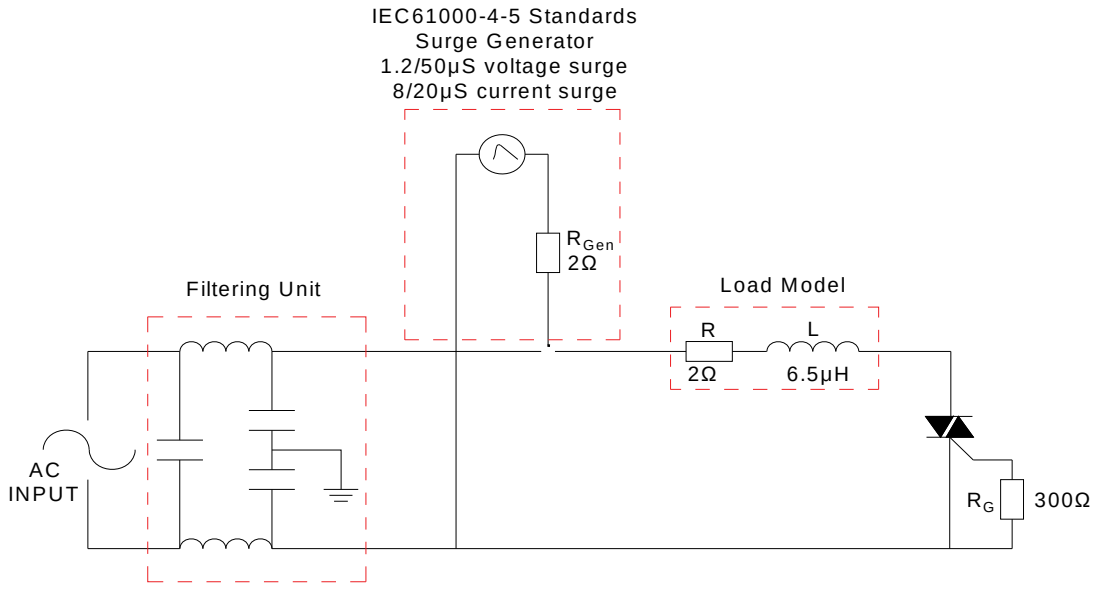


Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/µs)



Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



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PACKAGE MECHANICAL DATA



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